

2SK2590

Silicon N Channel MOS FET

Application

High speed power switching

Features

- Low on-resistance
- High speed switching
- Low drive current
- No Secondary Breakdown
- Suitable for Switching regulator, DC – DC converter, Motor Control

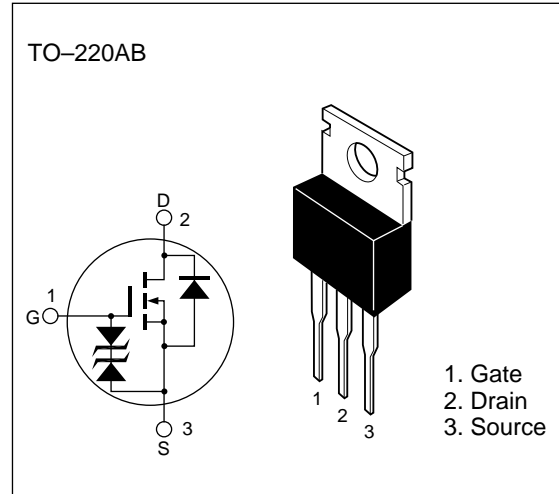


Table 1 Absolute Maximum Ratings (Ta = 25°C)

| Item | Symbol | Ratings | Unit |
|----------------------------------------|-------------------------|-------------|------|
| Drain to source voltage | V _{DSS} | 200 | V |
| Gate to source voltage | V _{GSS} | ±20 | V |
| Drain current | I _D | 7 | A |
| Drain peak current | I _{D(pulse)} * | 28 | A |
| Body-drain diode reverse drain current | I _{DR} | 7 | A |
| Channel dissipation | P _{ch} ** | 50 | W |
| Channel temperature | T _{ch} | 150 | °C |
| Storage temperature | T _{stg} | -55 to +150 | °C |

* PW ≤ 10 μs, duty cycle ≤ 1 %

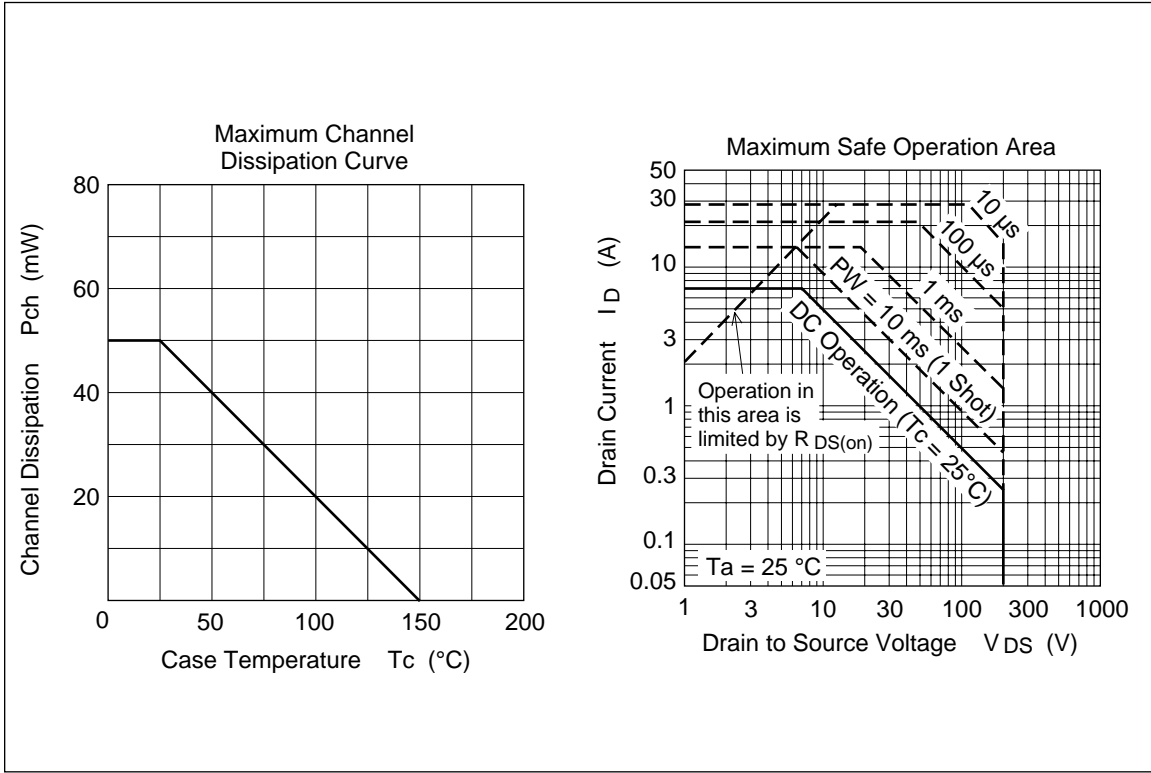
** Value at T_c = 25 °C

Table 2 Electrical Characteristics (Ta = 25°C)

| Item | Symbol | Min | Typ | Max | Unit | Test conditions |
|--------------------------------------------|---------------|-----|------|------|------|----------------------------------------------------------------------------------|
| Drain to source breakdown voltage | $V_{(BR)DSS}$ | 200 | — | — | V | $I_D = 10 \text{ mA}$, $V_{GS} = 0$ |
| Gate to source breakdown voltage | $V_{(BR)GSS}$ | ±20 | — | — | V | $I_G = \pm 100 \text{ } \mu\text{A}$, $V_{DS} = 0$ |
| Gate to source leak current | I_{GSS} | — | — | ±10 | μA | $V_{GS} = \pm 16 \text{ V}$, $V_{DS} = 0$ |
| Zero gate voltage drain current | I_{DSS} | — | — | 250 | μA | $V_{DS} = 160 \text{ V}$, $V_{GS} = 0$ |
| Gate to source cutoff voltage | $V_{GS(off)}$ | 2.0 | — | 4.0 | V | $I_D = 1 \text{ mA}$, $V_{DS} = 10 \text{ V}$ |
| Static drain to source on state resistance | $R_{DS(on)}$ | — | 0.33 | 0.45 | Ω | $I_D = 4 \text{ A}$ $V_{GS} = 10 \text{ V}^*$ |
| Forward transfer admittance | $ y_{fs} $ | 3.0 | 4.5 | — | S | $I_D = 4 \text{ A}$ $V_{DS} = 10 \text{ V}^*$ |
| Input capacitance | C_{iss} | — | 700 | — | pF | $V_{DS} = 10 \text{ V}$ |
| Output capacitance | C_{oss} | — | 260 | — | pF | $V_{GS} = 0$ |
| Reverse transfer capacitance | C_{rss} | — | 45 | — | pF | $f = 1 \text{ MHz}$ |
| Turn-on delay time | $t_{d(on)}$ | — | 20 | — | ns | $I_D = 4 \text{ A}$ |
| Rise time | t_r | — | 45 | — | ns | $V_{GS} = 10 \text{ V}$ |
| Turn-off delay time | $t_{d(off)}$ | — | 50 | — | ns | $R_L = 7.5 \Omega$ |
| Fall time | t_f | — | 35 | — | ns | |
| Body-drain diode forward voltage | V_{DF} | — | 1.1 | — | V | $I_F = 7 \text{ A}$, $V_{GS} = 0$ |
| Body-drain diode reverse recovery time | t_{rr} | — | 150 | — | ns | $I_F = 7 \text{ A}$, $V_{GS} = 0$, $diF / dt = 100 \text{ A} / \mu\text{s}$ |

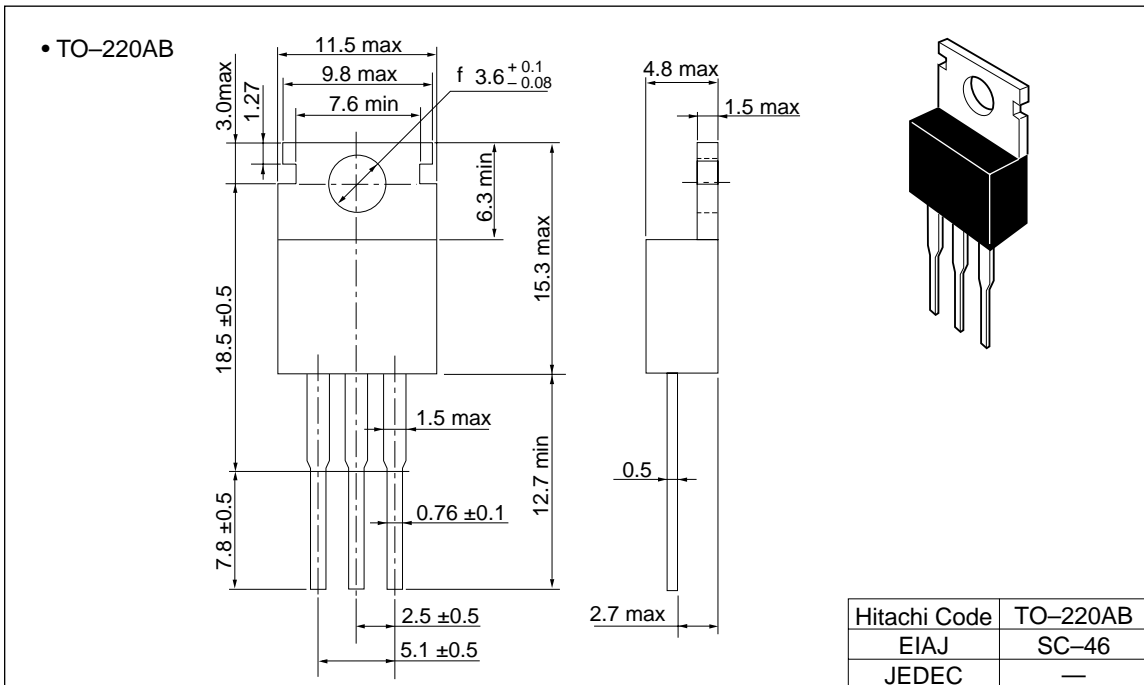
* Pulse Test

See characteristics curves of 2SK1957.



Package Dimensions

Unit : mm



Package Dimensions

Unit : mm

